

DOPING OF GALLIUM NITRIDE BY SOLID SOURCE DIFFUSION  
AND RESULTING GALLIUM NITRIDE STRUCTURES

Abstract

5           An improved p-type gallium nitride-based semiconductor device is disclosed. The device includes a structure with at least one p-type Group III nitride layer that includes some gallium, a first silicon dioxide layer on the p-type layer, a layer of a Group II metal source composition on the first SiO<sub>2</sub> layer, and a second SiO<sub>2</sub> layer on the Group II metal source composition layer.

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